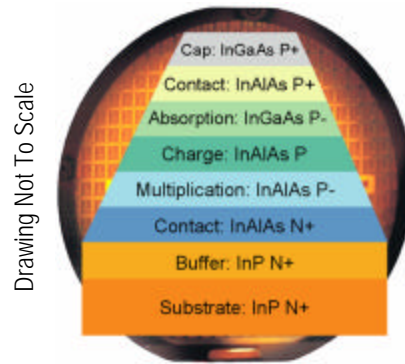


043644: 200 μ m Avalanche Photodiode (APD) Die

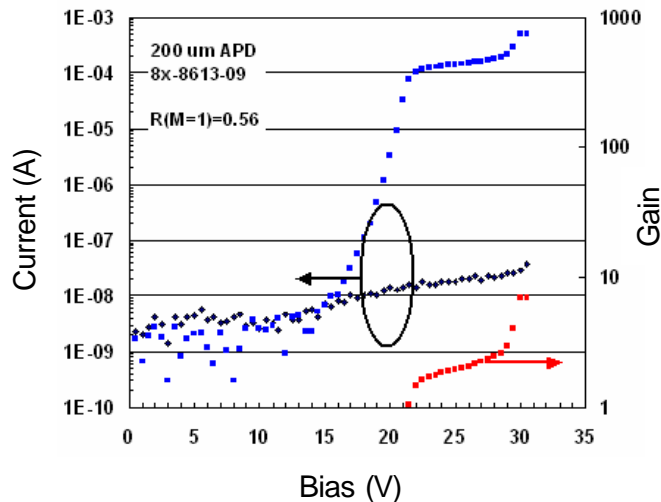
General Product Description

- InAlAs/InGaAs mesa design.
- Low dark current.
- Front illumination design.
- Available in TO-Can Packages.

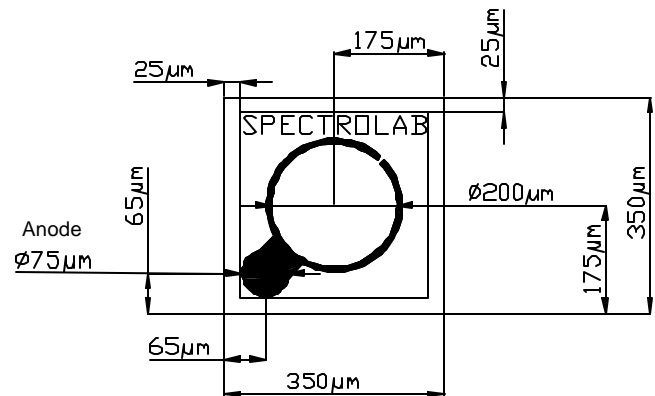


InAlAs APD Photodiode Die Structure

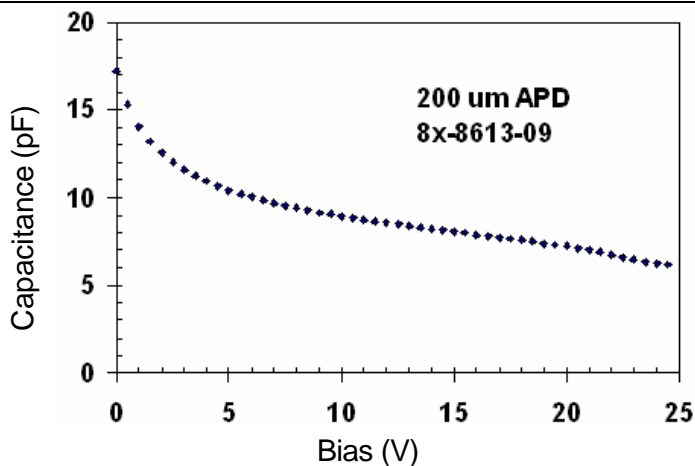
InAlAs APD Die I-V & Gain Data



Mechanical Specification



Device C-V Data



Device Specifications at 22° C

Parameter	Min.	Type	Max.	Unit
Diameter		200		μ m
Responsivity @ 1550 at M = 10	7	9		A/W
Dark Current at M = 10		25	200	nA
Capacitance at M = 10		4.0		pF
Bandwidth	200			MHz
Quantum Efficiency @ 1550nm	75%			%
Maximum Usable Gain (M)	10			

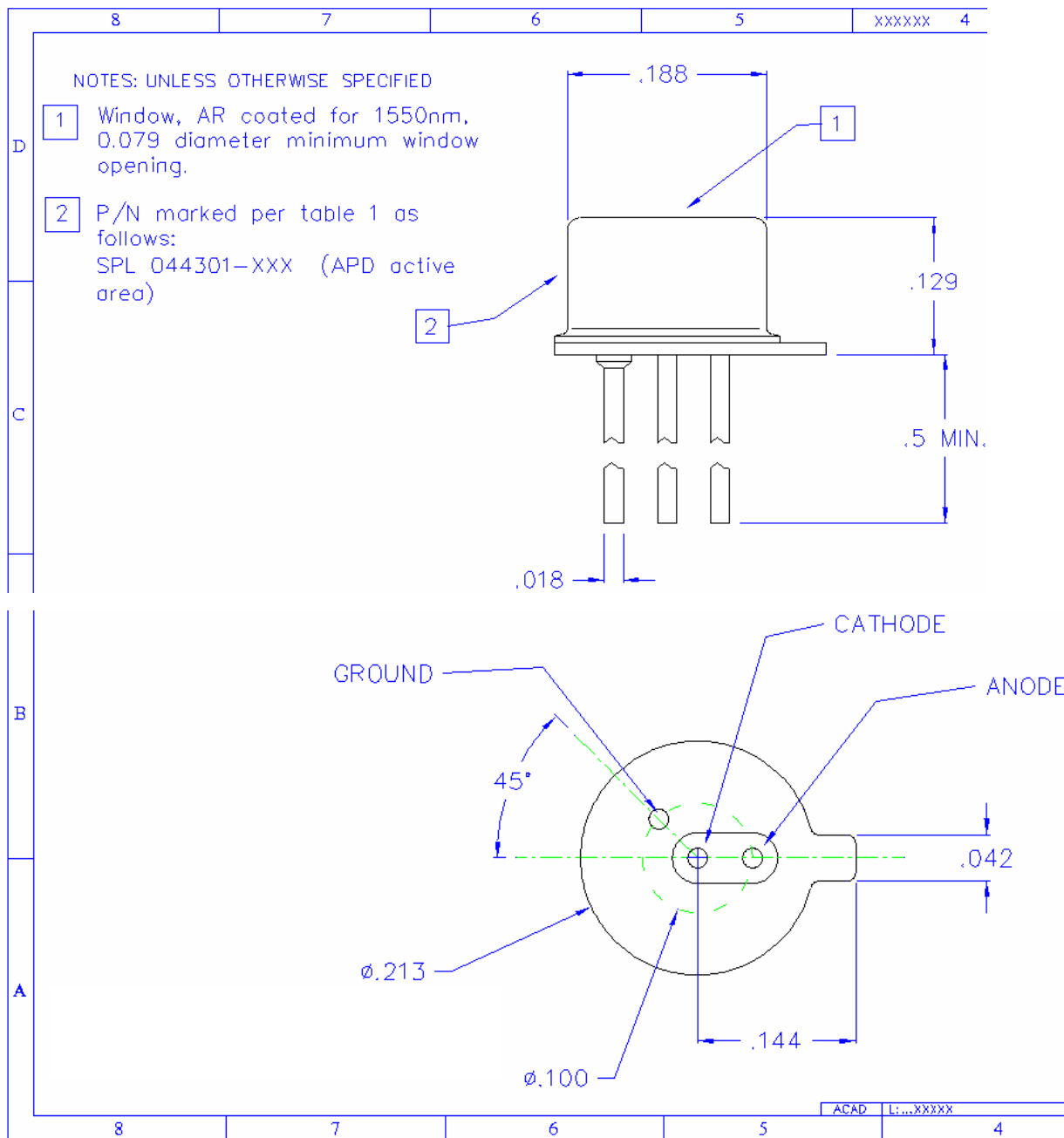
The information contained on this sheet is for reference only. Actual specifications for delivered products may vary. 01/16/06

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TO-46 Package mechanical specifications



The information contained on this sheet is for reference only. Actual specifications for delivered products may vary. 04/05/06

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